

TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (L<sup>2</sup>-π-MOSV)

# 2SJ377

Relay Drive, DC/DC Converter and Motor Drive Applications

Unit: mm

- 4 V gate drive
- Low drain-source ON-resistance :  $R_{DS(ON)} = 0.16 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 4.0 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = -100 \mu\text{A}$  (max) ( $V_{DS} = -60 \text{ V}$ )
- Enhancement mode :  $V_{th} = -0.8 \sim -2.0 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )

### Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	-60	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	-60	V	
Gate-source voltage	$V_{GSS}$	$\pm 20$	V	
Drain current	DC (Note 1)	$I_D$	-5	A
	Pulse (Note 1)	$I_{DP}$	-20	A
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	20	W	
Single-pulse avalanche energy (Note 2)	$E_{AS}$	273	mJ	
Avalanche current	$I_{AR}$	-5	A	
Repetitive avalanche energy (Note 3)	$E_{AR}$	2	mJ	
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$	
Storage temperature range	$T_{stg}$	-55~150	$^\circ\text{C}$	

### Thermal Characteristics

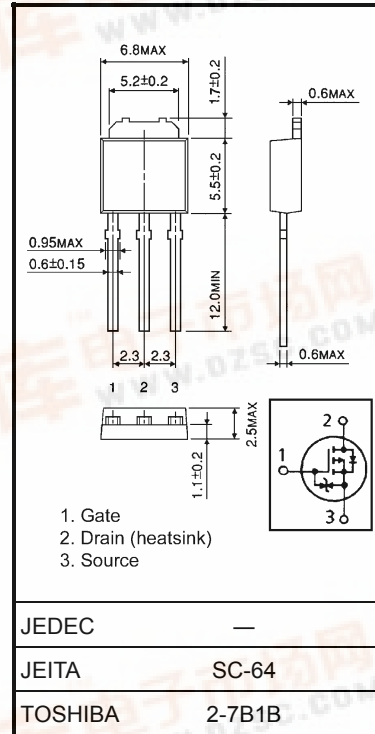
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^\circ\text{C} / \text{W}$

Note 1: Ensure that the channel temperature does not exceed 150°C.

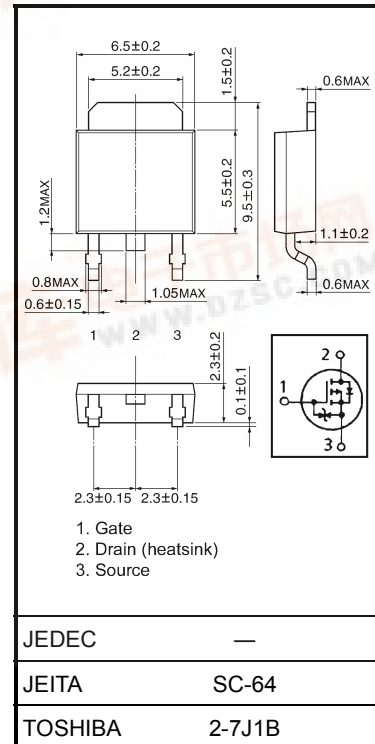
Note 2:  $V_{DD} = -25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 14.84 \text{ mH}$ ,  
 $R_G = 25 \Omega$ ,  $I_{AR} = -5 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.36 g (typ.)



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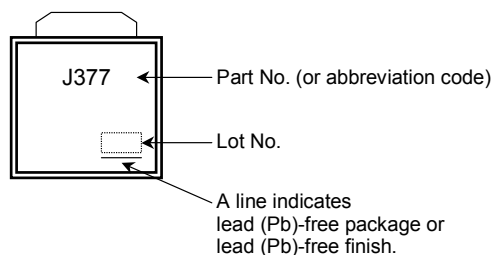
## Electrical Characteristics (Ta = 25°C)

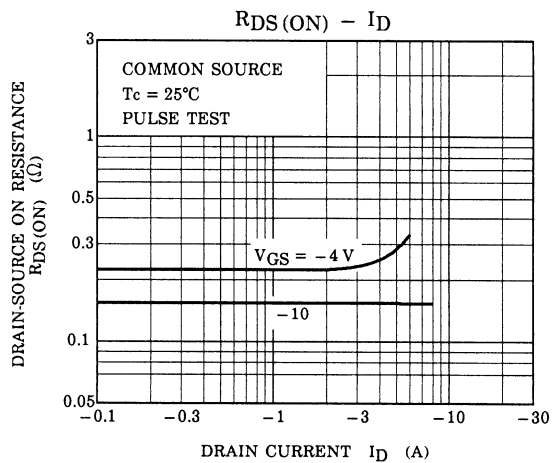
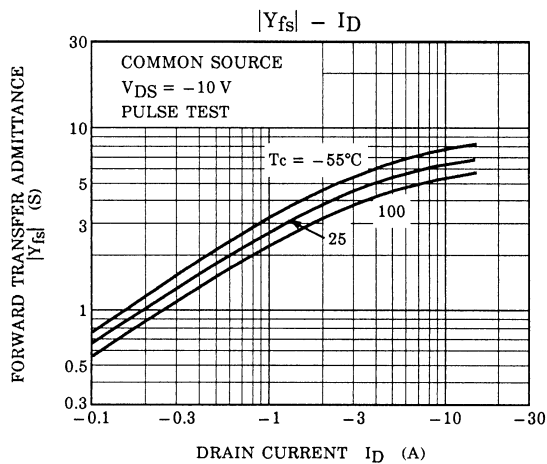
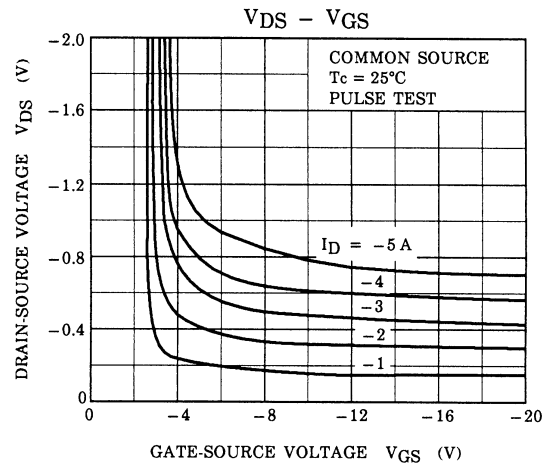
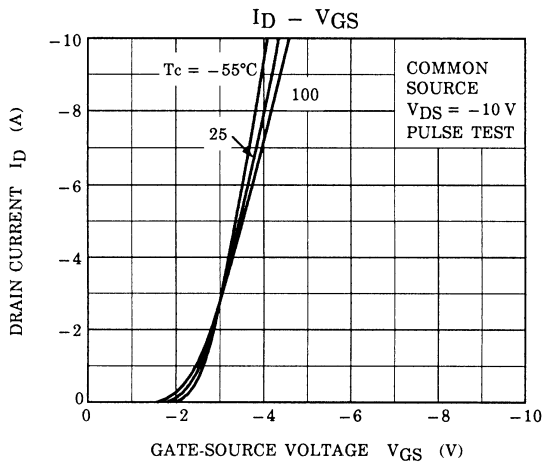
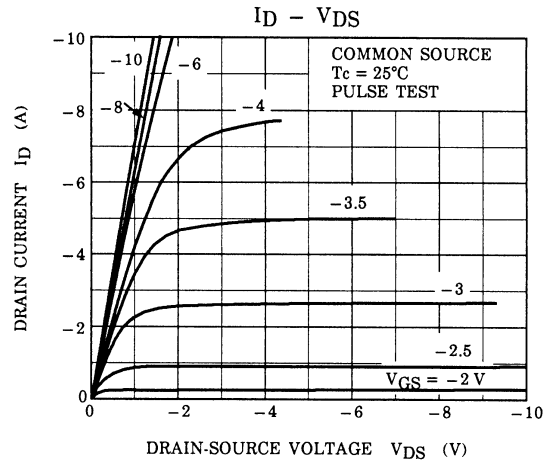
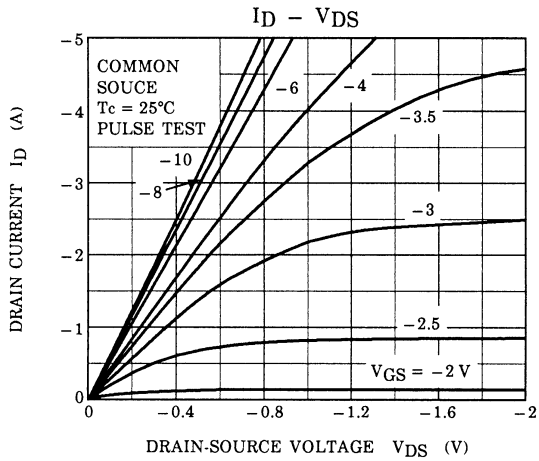
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cutoff current		$I_{DSS}$	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	—	—	-100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-60	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = -4\text{ V}, I_D = -2.5\text{ A}$	—	0.24	0.28	$\Omega$
			$V_{GS} = -10\text{ V}, I_D = -2.5\text{ A}$	—	0.16	0.19	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -2.5\text{ A}$	2.0	4.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	630	—	pF
Reverse transfer capacitance		$C_{rss}$		—	95	—	
Output capacitance		$C_{oss}$		—	290	—	
Switching time	Rise time	$t_r$	<p><math>I_D = -2.5\text{ A}</math>  <math>V_{GS} = 0\text{ V}, -10\text{ V}</math>  <math>50\Omega</math>  <math>R_L = 12\Omega</math>  <math>V_{DD} = -30\text{ V}</math>                      Duty <math>\leq 1\%</math>, <math>t_W = 10\mu\text{s}</math></p>	—	25	—	ns
	Turn-on time	$t_{on}$		—	45	—	
	Fall time	$t_f$		—	55	—	
	Turn-off time	$t_{off}$		—	200	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx -48\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	—	22	—	nC
Gate-source charge		$Q_{gs}$		—	16	—	
Gate-drain ("Miller") charge		$Q_{gd}$		—	6	—	

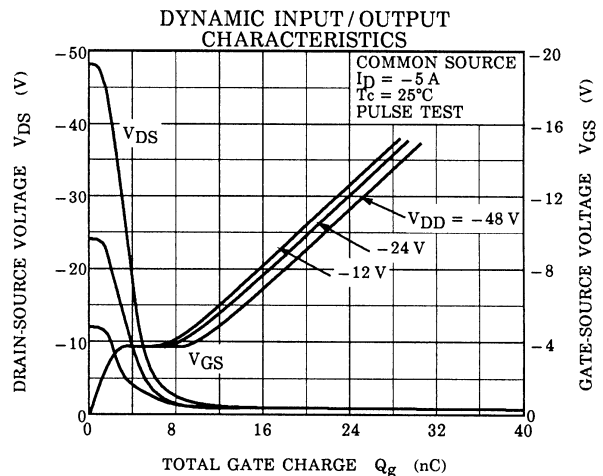
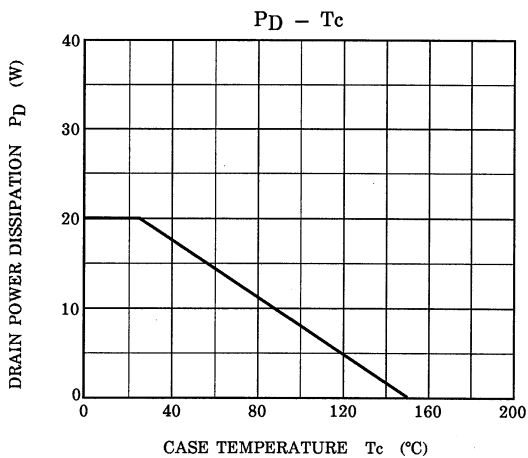
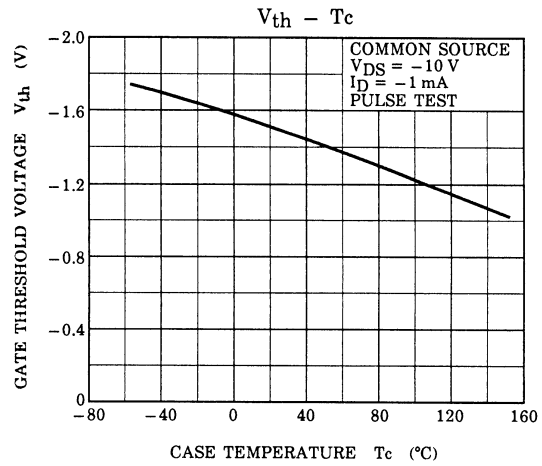
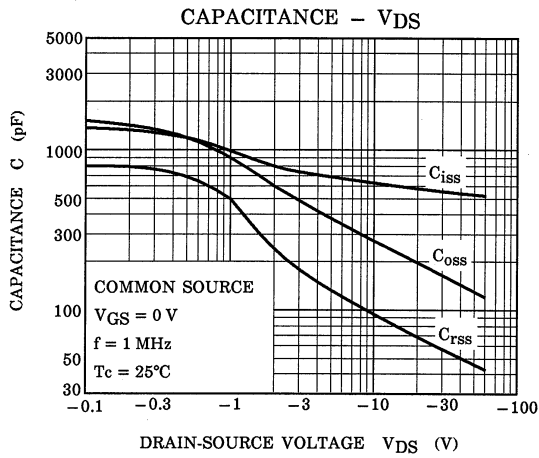
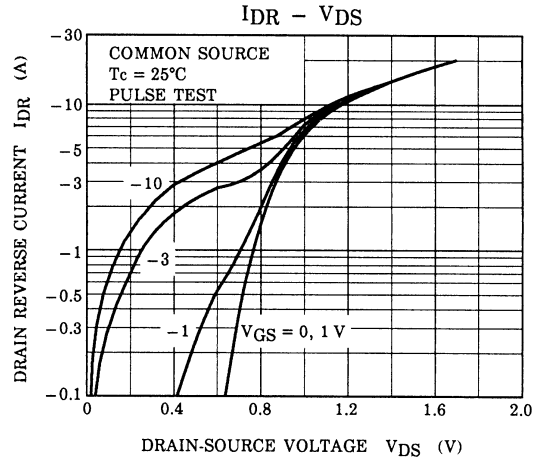
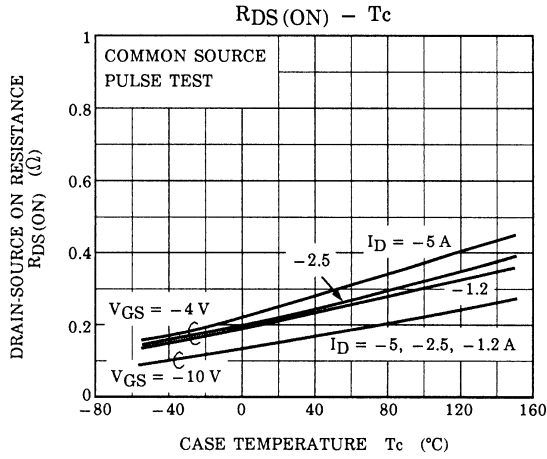
## Source-Drain Ratings and Characteristics (Ta = 25°C)

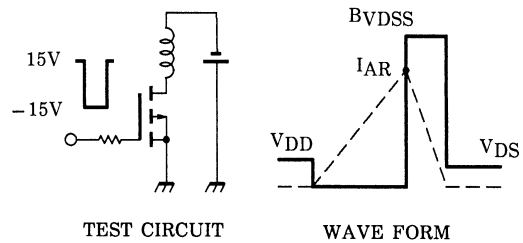
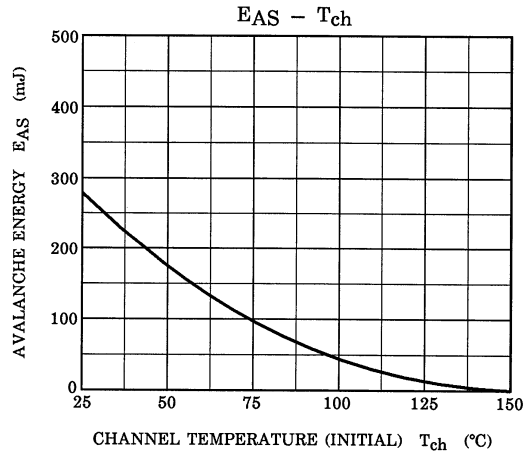
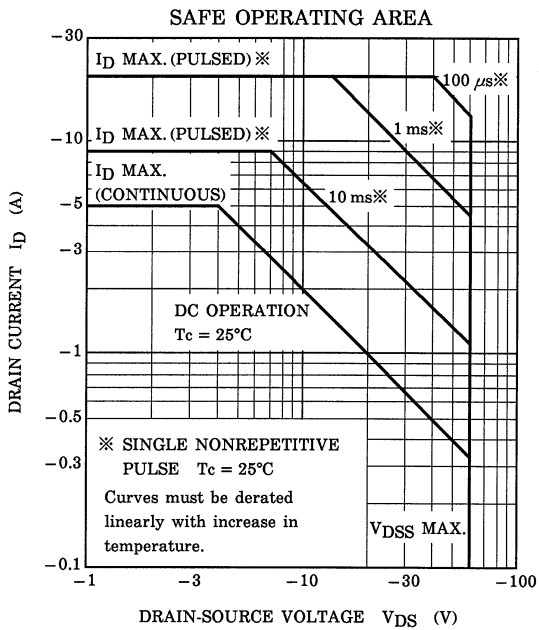
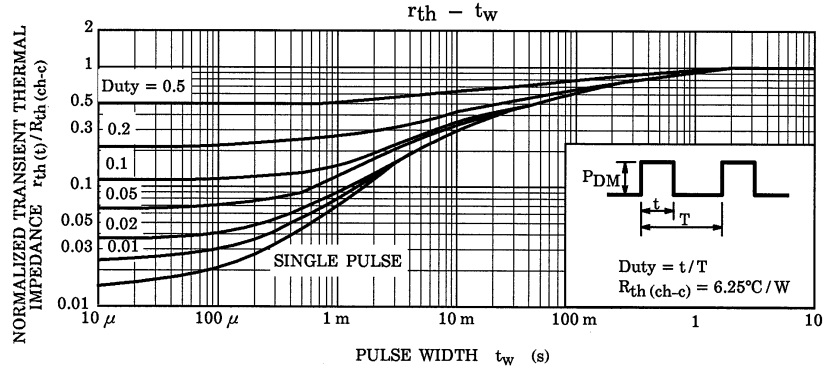
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	-5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	-20	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = -5\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = -5\text{ A}, V_{GS} = 0\text{ V}$	—	80	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR} / dt = 50\text{ A} / \mu\text{s}$	—	0.1	—	$\mu\text{C}$

## Marking









$R_G = 25\Omega$   
 $V_{DD} = -25V, L = 14.84mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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